MITSUBISHI ELECTRIC
Changes for the Better

HVIC

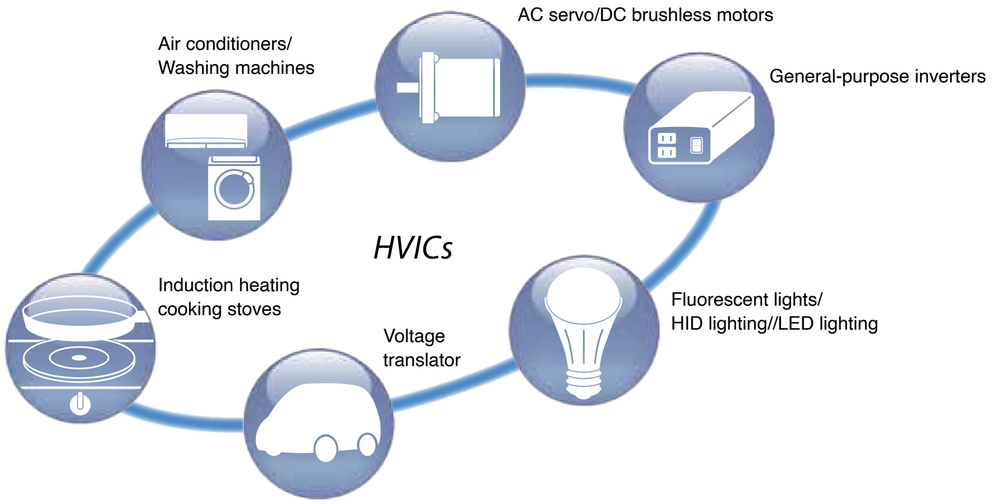
HVIC

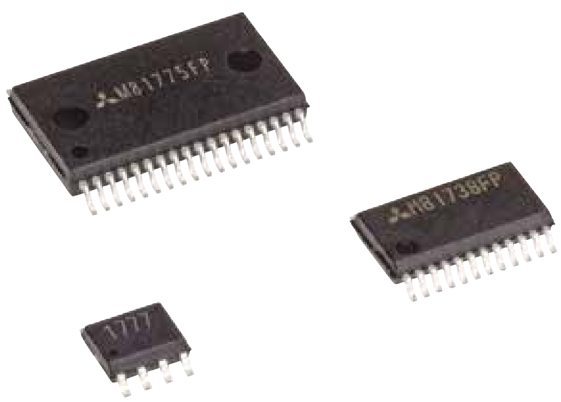
Innovative Power Devices for a Sustainable Future

Mitsubishi Electric HVICs contribute to the high reliability of various power supply equipment by equipping them with various the protection functions.

High-voltage integrated circuits (HVICs) are capable of directly driving the gates of power MOSFETs and IGBTs using signals input from microcomputers, thereby replacing power MOSFET and IGBT gate drivers that use pulse transformers and photocouplers. They are insulated by a level shift circuit inside the semiconductor chip. Since a variety of protection functions, such as power supply undervoltage, interlocking, input signal filter, and error output, are built into the IC, reliability of the power supply equipment is enhanced.
Mitsubishi Electric has many half-bridge products that are commonly used in drive circuits. Our HVIC products comply with the European Union's Restriction of Hazardous Substances Directive for electrical equipment, 2011/65/EU and 2015/863/EU.

Main Features	**High voltage floating circuit is built-in because it is a high side gate drive.** **Built-in signal transmission (level shift) function for transmitting signals to the floating circuit** **High side gate driver section has a high voltage isolation structure.** **Level shift section has a high voltage NMOS structure.**





1200V HVIC with Desaturation Detection for Power Semiconductors M81748FP

M81748FP achieves the high durability of 1200V that is suitable for AC400V inverter systems.

●High durable 1200V rating that is applicable to an industrial use like AC400V inverter systems

- The HVIC achieves low leakage current limited to a maximum 10uA of HVIC by applying a 1200V divided RESURF*1 structure to optimize its surface structure.
- PolyRFP*2 structure of chip surface greatly enhances the durability.

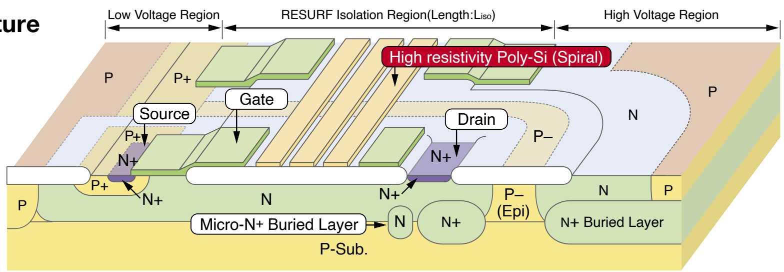
●High tolerance to switching noise helps achieve highly reliable inverter systems

- High latch-up immunity (parasitic Vertical -PNP transistor action) realized with chip's low-impedance buried layers.

●Desaturation detection for reduced power loss reduction in power semiconductors

- P-side and N-side desaturation detection prevents overcurrent thermal destruction of the power semiconductors by using 1200V P-channel MOSFET.
- The HVIC directly detects shorts and earth faults in power semiconductors on P-side and transmits fault signals to N-side, shutting down systems.
- Desaturation detection is sperior to the detection method which is used the shunt resistor for the power loss reduction in power semiconductors.

The cross section structure of 1200V Nch MOSFET that applied the divided RESURF*1 structure



*1 RESURF: REduced SUrface Field *2 PolyRFP: Polycrystalline silicon Resistor Field Plate

Half-bridge Driver High-voltage (600V) IC with BSD Function M81777FP

Built-in BSD function helps to reduce the number of parts in inverter systems.

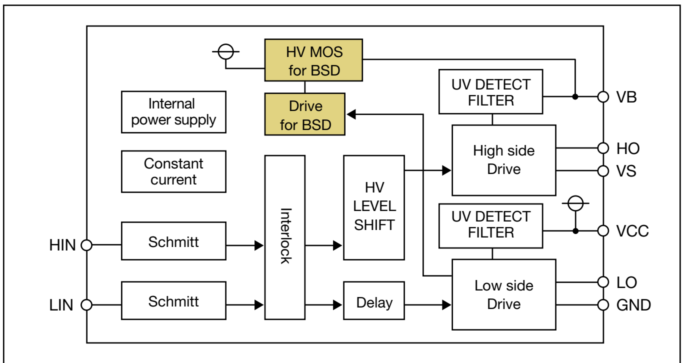
<Main Features>

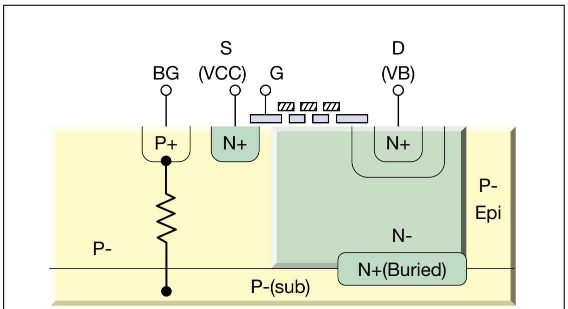
●Built-in BSD function helps to reduce the number of parts in inverter systems

- M81777FP for inverter systems is equipped with a BSD function that enables inverter systems and high-voltage wiring to be designed with fewer parts.

●BSD function's high-voltage metal oxide semiconductor (MOS) achieves high noise resistance

- Mitsubishi Electric's proprietary high-voltage MOS structure suppresses current leakage during charging.
- The MOS structure is free of parasitic elements that can cause latch-up malfunctions due to noise when switching inverters (negative potential surge noise generated in freewheel diode during reflux mode).





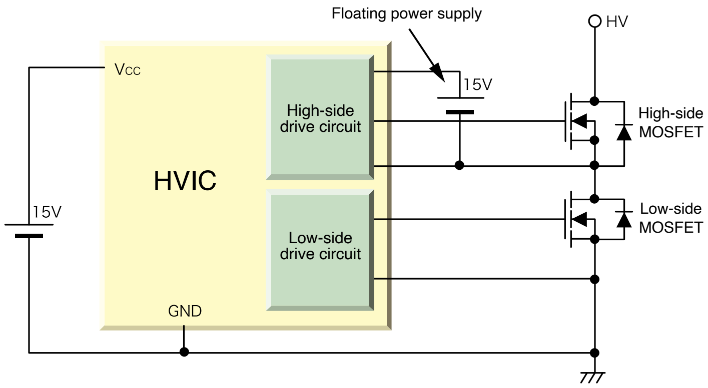
HV MOS for BSD (No parastic PNP Tr)

Attention points of HVIC use

1 The floating power supply method

The emitter/source potential of high-side IGBT/MOSFET referenced to GND changes to the voltage of the HV terminal from 0V when operating the application. Therefore, to drive high-side IGBT/MOSFET, the power supply of the high-side drive circuit of HVIC should have potential which is higher by VBS than the emitter/source potential of high-side IGBT/MOSFET. One of the methods to apply this voltage is the floating power supply method. Fig_right shows the example of the floating power supply method.

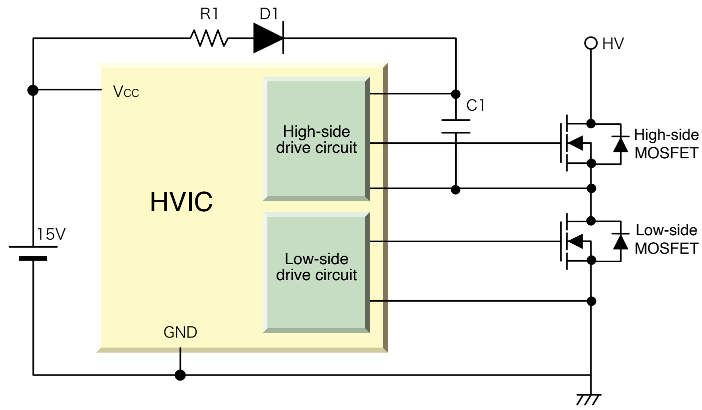
■Floating power supply method



2 Bootstrap circuit method and basic operation

Bootstrap circuit method is used in place of the folating power supply method. The bootstrap capacitor(C1) is charged through the resistor (R1) and bootstrap diode(D1) by VCC, and the high-side drive circuit of HVIC is driven by the voltage of the capacitor(C1). Fig_right shows the example of the bootstrap circuit method.
M81777FP shown in p.5 is equipped with a BSD function that enables bootstrap circuits to be designed without R1 and C1.

■Bootstrap circuit system



3 Electrical charge and discharge current route when HVIC is operated

Fig_right shows the electrical charge and discharge current route of C1 when HVIC is regularly operated.

■Setting of bootstrap capacitor (C1)

Initial charge and the voltage between bootstrap capacitor (C1)

To drive high-side MOSFET, the bootstrap capacitor is charged by turning on low-side MOSFET.
The inrush charging current is from the charging path on the right
ID=(VCC/R1)e-t/(R1･C1) from the initial condition t = 0
ID=VCC/R1

VC1 is shown below. (VF:Voltage between D1 terminals, VDS:Voltage beween drain and souce of low-side MOSFET)

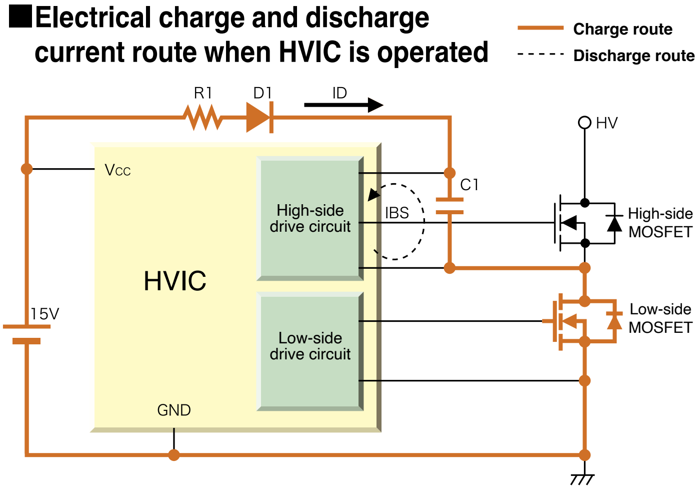
VC1=VCC-VF-VDS･･･(1)

Simple calculation of bootstrap capacitor (C1)

The capacitance value C1 is shown below. (T1:Maximum on-time of high-side MOSFET, IBS:High-side drive circuit consumption current of HVIC, ΔV:Electrical discharge allowance voltage between C1 terminals)
C1 = IBS x T1 ／ ΔV + margin ･･･(2)

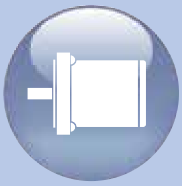
IBS changes depending on gate capacitance of MOSFET and carrier frequency. And (1) and (2) expression are simplified. So please set the capacitance value C1 based on evaluation of your system.

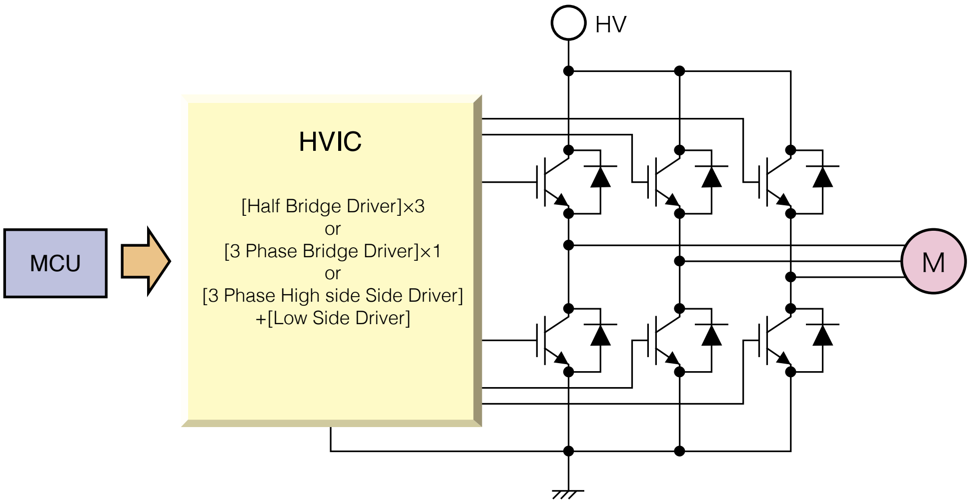
■Electrical charge and discharge current route when HVIC is operated



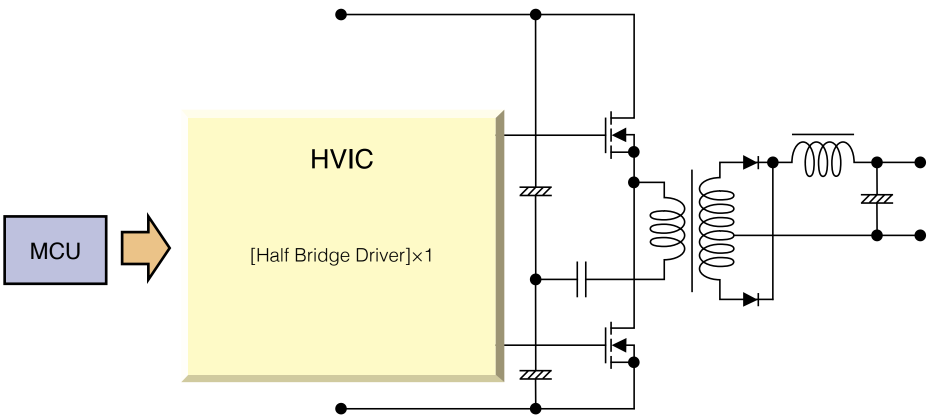
Application circuit examples

Configuration example of gate driver for motor

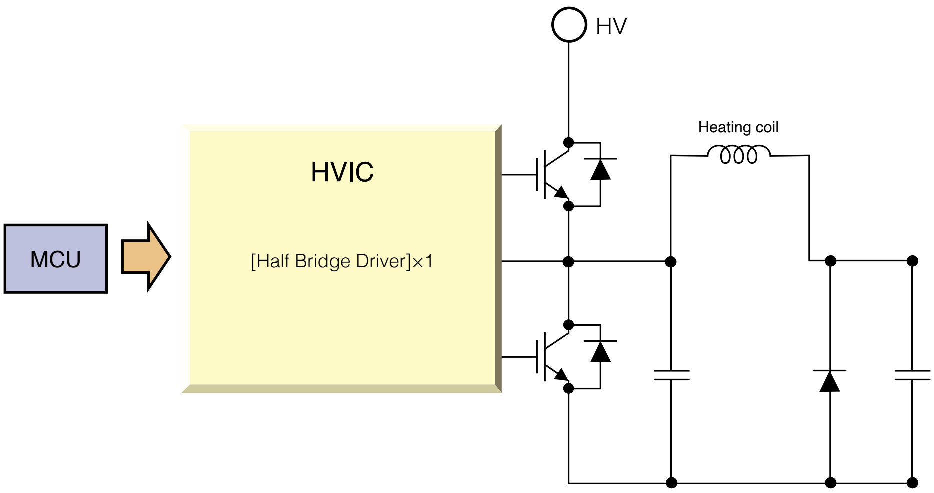




Configuration example of gate driver for DC-DC converter



Configuration example of gate driver for IH cooking heater



Line-up of HVIC

1200V floating supply voltage

Device drive system	Number of input signals	Generation	Type name	Floating supply voltage[V]	Output current [A](typ)	Dead time control	Internal function	Package outline			
								Package type	Number of terminals	Package dimension width x length (Unit:mm)	Lead pitch(mm)
Half Bridge	2	3rd	M81738FP	1200	±1.0	Input Signal	UV,IL,NF,SC,FO, FORST,FOIN	SSOP	24	5.3×10.1	0.8
			M81748FP	1200	±2.0	Input Signal	UV,IL,NF,DESAT, FO,CFO,FOIN,SS	SSOP	24	5.3×10.1	0.8

600V floating supply voltage

Device drive system	Number of input signals	Generation	Type name	Floating supply voltage[V]	Output current [A](typ)	Dead time control	Internal function	Package outline			
								Package type	Number of terminals	Package dimension width x length (Unit:mm)	Lead pitch(mm)
3 Phase	2×3Φ	4th	M81749FP	600	+0.2/-0.35	Input Signal	UV,IL,SC, FO,CFO	SSOP	24	5.3×10.1	0.8
			M81775FP	600	+0.2/-0.5	Input Signal	UV,IL,NF	SSOP	36	8.4×15	0.8
Half Bridge	2	4th	M81776FP	600	+0.2/-0.35	Input Signal	UV,IL	SOP	8	3.9×4.85	1.27
			M81777FP	600	+0.2/-0.35	Input Signal	UV,IL,BSD	SOP	8	3.9×4.85	1.27
			M81747FP	600	+0.2/-0.35	Input Signal	UV,IL,NF	SOP	8	3.9×4.85	1.27
			M81774FP	600	±1.0	Input Signal	UV,NF,SC,FO, FORST,FOIN	SSOP	24	5.3×10.1	0.8
			M81770FP	600	±3.25	Input Signal	UV,IL,SD	SSOP	24	5.3×10.1	0.8
			M81767FP	600	±3.5	Input Signal	UV,NF	SOP	8	3.9×4.85	1.27
			M81767JFP (for automotive)	600	+0.2/-0.35	Input Signal	UV,IL,NF	SOP	8	3.9×4.85	1.27
			M81747JFP (for automotive)	600	±3.5	Input Signal	UV,IL,NF	SOP	8	3.9×4.85	1.27
	1	4th	M81734FP	600	±0.5	Internal	UV	SOP	8	3.9×4.85	1.27

24V floating supply voltage

Device drive system	Number of input signals	Generation	Type name	Floating supply voltage[V]	Output current [A](typ)	Dead time control	Internal function	Package outline			
								Package type	Number of terminals	Package dimension width x length (Unit:mm)	Lead pitch(mm)
Single Low Side	1	4th	M81764FP	24	+1.75/-0.8	—	UV,SC,FO,CFO	SOP	8	3.9×4.85	1.27

<Term> UV : Under Voltage, IL : Inter Lock, NF : Input Noise Filter, SC : Short Current, SD : Shut Down, SS: Soft Shutdown,
FO : Failure Output, FOIN : FO Input, FORST : FO Reset, CFO : Capacitor FO, DESAT: Desaturation, BSD: BootStrap Diode

For details of internal functions and package outline, please refer to the data sheet of each product.

Authorised Distributors for Mitsubishi Electric Power Semiconductors

Austria	GLYN AUSTRIA	Campus 21 / Businesspark Wien Süd Liebermannstr. A02/301, A-2345 Brunn am Gebirge Phone +43 (0) 2236 311 112 0 Fax +43 (0) 2236 311 112 20	Email: sales@glyn.at www.glyn.at
	HY-LINE COMPONENTS GMBH	Inselkammerstr. 10, D-82008 Unterhaching Phone +49 (0)89 61 45 03 10 Fax +49 (0) 89 61 45 03 20	Email: power@hy-line.de www.hy-line.de
Baltic countries (Lithuania, Estonia, Latvia)	ELGERTA UAB	Visorių st. 2, LT-08300 Vilnius, Lithuania Phone +370 5 265 2683, 265 2689	Email: lithuania@elgerta.com www.elgerta.com
Benelux	INDEL DISTRIBUTION B.V.	Wattstraat 50, 2171 TR Sassenheim Phone +31 (0)252 214849	Email: tim@indel.com www.indel.com
	NIJKERK ELECTRONICS B.V. (Netherlands)	Willem Fenengastraat 12, 1096 BN Amsterdam Phone +31 (0)205 041424	Email: jan.degoede@nijkerk.nl www.nijkerk-ne.com
	NIJKERK ELECTRONICS N.V. (Belgium)	Romeynsweel 7, 2030 Antwerpen Phone +32 35447066	Email: alain.huysmans@nijkerk.be www.nijkerk-ne.com
Bulgaria	OHM BG EOOD	Svetlina Street No. 11, 8800 Sliven, Bulgaria Phone +359 4468 7533 Fax +359 4468 7533	Email: teokay@ohm.com.tr www.ohm.com.tr
Czech Republic	STARMANS ELECTRONICS, S.R.O.	V Zahradách 836/24, 180 00 Praha 8, Czech Republic Phone +420 (0) 225 442 260 Fax +420 (0) 283 841 067	Email: components@starmans.cz www.starmans.net
Denmark	GLYN DENMARK	Slotsmarken 18, DK-2970 Hørsholm Phone +45 702 016 33 Fax +45 702 016 37	Email: sales@glyn-nordic.dk www.glyn-nordic.dk
France	ARCEL	ZI le tronchon – 2 rue des aulnes 69410 Champagne Au Mont D'or Phone +33 (0) 478 35 0221 Fax +33 (0) 478 35 6954	Email: info@arcel.eu www.arcel.eu
	COMPELEC	MultiParc du Jubin, Bâtiment A 27, chemin des Peupliers 69 570 Dardilly, France Phone +33 (0) 472 088 080 Fax +33 (0) 472 088 215	Email: yfouletier@compelec.com www.compelec.com
Germany	GLYN GMBH & CO KG	Am Wörtzgarten 8, D-65510 Idstein/Ts. Phone +49 (0) 6126 590 388 Fax +49 (0) 6126 590 188	Email: power@glyn.de www.glyn.de
	HY-LINE POWER COMPONENTS VERTRIEBS GMBH	Inselkammerstr. 10, D-82008 Unterhaching Phone +49 (0) 89 61 45 03 10 Fax +49 (0) 89 61 45 03 20	Email: power@hy-line.de www.hy-line.de
	INELTRON GMBH	Hugenottenstr. 30, D-61381 Friedrichsdorf Phone +49 (0) 6172 49 98 23 0 Fax +49 (0) 6172 75 93 3	Email: info@ineltron.de www.ineltron.de
Hungary	INELTRON HUNGARY	Fecske 16, H-1194 Budapest Phone +36 70 3666055	Email: i.laszlo@ineltron.hu
Israel	RAM N.S TECHNOLOGIES LTD	1, Hamasger St., Raanana 43653, Israel Phone +972-(0)77-920 8111 Fax +972-(0)77-920 8112	Email: nati@ram-tech.co.il www.ram-tech.co.il

Italy	CELTE S.P.A.	Via Gobetti 2/A, 20063 Cernusco Phone +39 0292108020 Fax +39 0292108088	Email: info@celte.com www.celte.com
	MELCHIONI SPA	Via P. Colletta 37, 20135 Milano Phone +39 025794 725 Fax +39 025794 367	Email: G.Camagna@melchioni.com www.melchioni.it
Poland	DACPOL	Ul. Pulawska 34, PL-05500 Piaseczno Phone +48 22 7035 100 Fax +48 22 7035 101	Email: dacpol@dacpol.eu www.dacpol.eu
Romania	INELTRON ROMANIA	Str. Lunetei 4, RO-400504 Cluj – Napoca Phone +36 70 366 60 55	Email: i.laszlo@ineltron.hu
Spain and Portugal	AICOX SOLUCIONES SA	Avda. Somosierra, 12, 1°A, E-28703 San Sebastián de los Reyes Phone +34 91 65 92 970 Fax +34 91 65 31 019	Email: informa@aicox.com www.aicox.com
Portugal	INELEC SA	Bocangel, 38, E-28028 Madrid Phone +34 91 726 35 00 Fax +34 91 726 33 34	Email: inelec@inelec.net www.inelec.net
Sweden	GLYN SWEDEN	Tammsväg 13, SE-81576 Söderfors Phone +46 (0) 293 300 84 Fax +46 (0) 293 300 87	Email: sales@glyn.se www.glyn.se
Switzerland	ELEKTRON AG	Riedhofstr. 11, CH-8804 Au (Zürich) Phone +41 (0) 44 781 02 34	Email: power@elektron.ch www.elektron.ch
Turkey	OHM ELEKTRONIK VE TIRCARET A.Ş.	Gürsel Mah. Imrahor Cad. Premier Kampus Ofis No: 29/A, K.2, Ofis No: 92, Kağıthane, TR-34400, Istanbul Phone +90 212 293 95 91 Fax +90 212 244 27 72	Email: ohm.info@ohm.com.tr www.ohm.com.tr
Ukraine	DACPOL UKRAINE	Snovskaya str. 20, 02090 Kiev, Ukraine Phone +380 44 501 93 44 Fax +380 44 502 64 87	Email: kiev@dacpol.com www.dacpol.ua
	SYMMETRON UKRAINE	Sverstyuka Evhena Str. 13, 02660 Kiev, Ukraine Phone +38 0 (44) 239-2065 Fax +38 0 (44) 239-2069	Email: kiev@symmetron.ua www.symmetron.ua
United Kingdom	JOHN G. PECK LTD	Unit B1 Wymeswold Industrial Park, Wymeswold Lane, Burton on the Wolds, Loughborough, Leics. LE12 5TY Phone +44 1509 88 10 10	Email: info@jgpl.com www.jgpl.com

Mitsubishi Electric Europe B.V. (European Headquarters)
– Semiconductor European Business Group –
Mitsubishi-Electric-Platz 1 / D-40882 Ratingen
Phone +49 (0) 21 02 / 486 0 / Fax +49 (0) 21 02 / 486 41 40

Mitsubishi Electric Europe B.V.
German Branch
Semiconductor Sales Office
Mitsubishi-Electric-Platz 1
D-40882 Ratingen
Phone +49 (0) 21 02 / 486 34 30
Fax +49 (0) 21 02 / 486 72 20

Mitsubishi Electric Europe B.V.
UK Branch
Semiconductor Sales Office
Travellers Lane, Hatfield
GB-Herts. AL 10 8XB
Phone +44 17 07 / 27 89 07

Mitsubishi Electric
(Russia) LLC
Semiconductor Sales Office
Letnikovskaya St.2, bld.1
115114 Moscow, Russia
Phone +7 495 721 20 70
Fax +7 495 721 20 71

Mitsubishi Electric Europe B.V.
French Branch
Semiconductor Sales Office
2 Rue de l'Union
92565 Rueil-Malmaison Cedex
Phone +33 1 / 55 68 55 68
Fax +33 1 / 55 68 57 39

Mitsubishi Electric Europe B.V.
Italian Branch
Semiconductor Sales Office
Campus, Energy Park
Via Energy Park 14, Vimercate 20871 (MB)
Phone: +39 039 60 53 10

Spanish Representative Agent
for Mitsubishi Electric Europe
in Spain and Portugal
C/ Las Hayas, 127
28922 Alcorcón (Madrid)
Phone +34 9 16 43 68 05

Mitsubishi Electric Semiconductors & Devices Website

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MITSUBISHI ELECTRIC CORPORATION
HEAD OFFICE: TOKYO BLDG., 2-7-3, MARUNOUCHI, CHIYODA-KU, TOKYO 100-8310, JAPAN
www.MitsubishiElectric.com

Revised publication, effective Apr. 2023.
Superseding publication of HG-398D Apr. 2022.
Specifications subject to change without notice.

HG-398E FU-2304 Printed in Japan <IP>